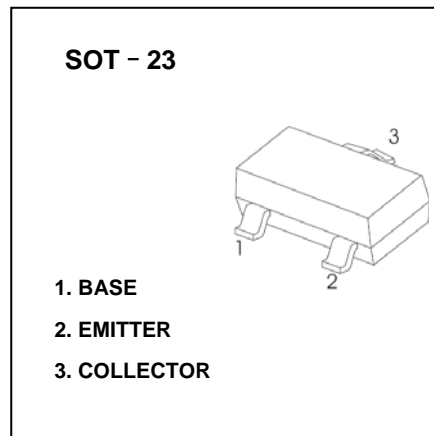


SOT-23 Plastic-Encapsulate MOSFETS

IRLML5203 P-Channel 30-V(D-S) MOSFET

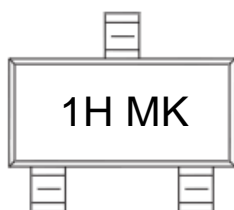
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	85mΩ@-10 V	-3.0A
	145mΩ@-4.5V	



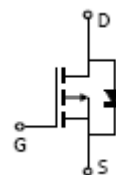
General Description

The UMW IRLML5203 uses advanced trench technology to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications.

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-3.0	A
Drain Current-Pulsed	I_{DM}	-24	A
Power Dissipation	P_D	300	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

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$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
Gate -source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.1A$			85	m Ω
		$V_{GS} = -4.5V, I_D = -3A$			145	m Ω
Forward tranconductance (note 1)	g_{FS}	$V_{DS} = -5V, I_D = -4A$	5.5			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1		-3	V
Diode forward voltage (note 1)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		700		pF
Output capacitance	C_{oss}			120		pF
Reverse transfer capacitance	C_{rss}			75		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V,$ $R_L = 3.6\Omega, R_{GEN} = 3\Omega$		8.6		ns
Turn-on rise time	t_r			5.0		ns
Turn-off delay time	$t_{d(off)}$			28.2		ns
Turn-off fall time	t_f			13.5		ns

Notes:

1. Pulse test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. These parameter have no way to verify.

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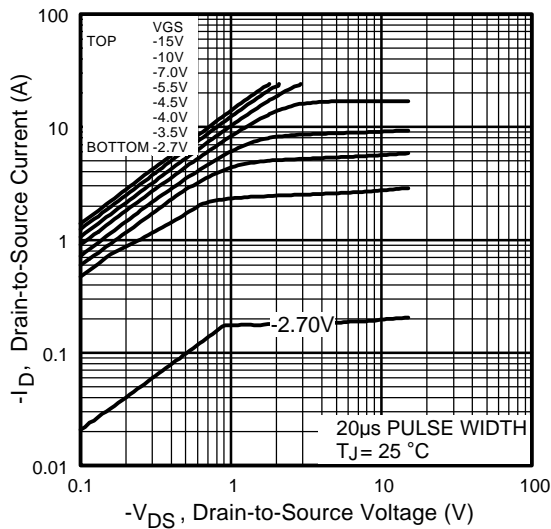


Fig 1. Typical Output Characteristics

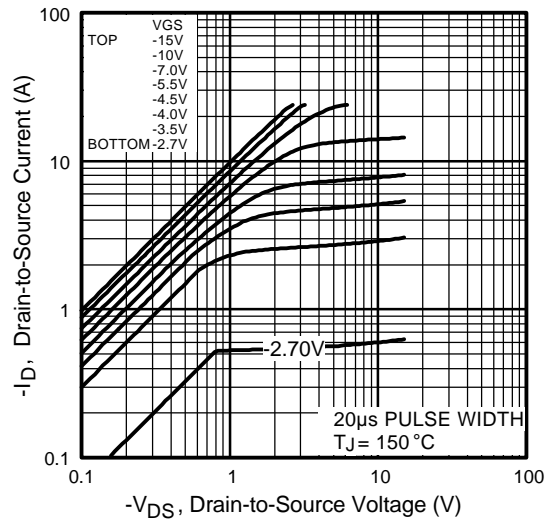


Fig 2. Typical Output Characteristics

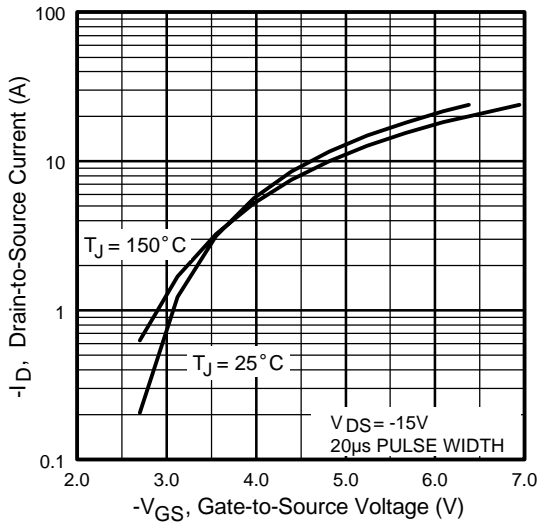


Fig 3. Typical Transfer Characteristics

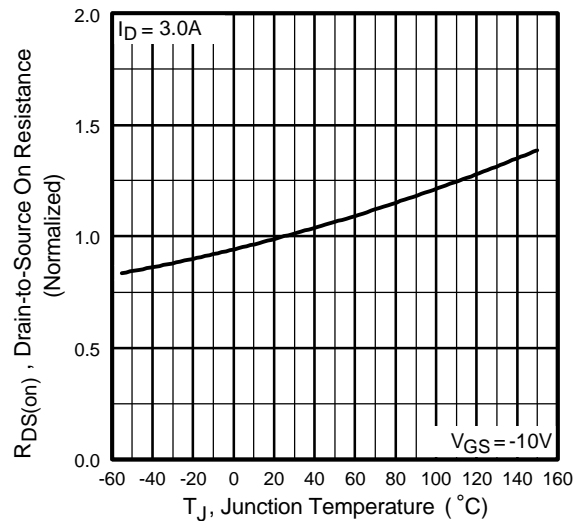


Fig 4. Normalized On-Resistance Vs. Temperature

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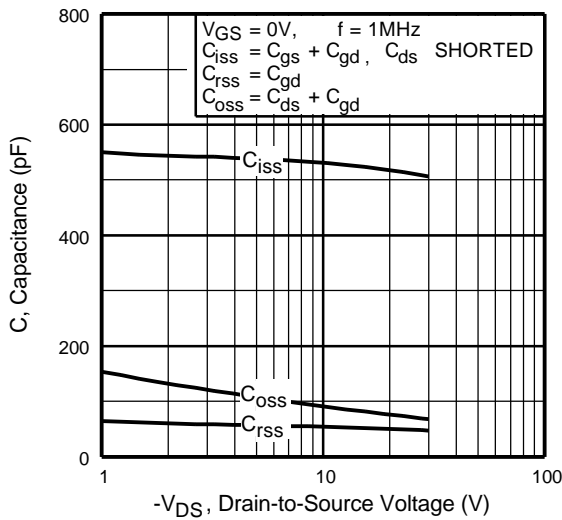


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

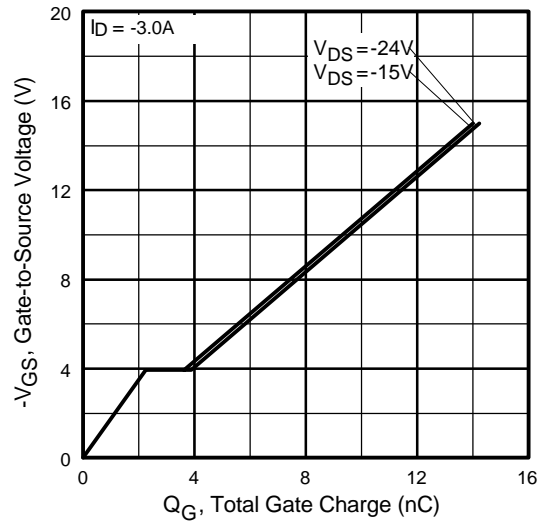


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

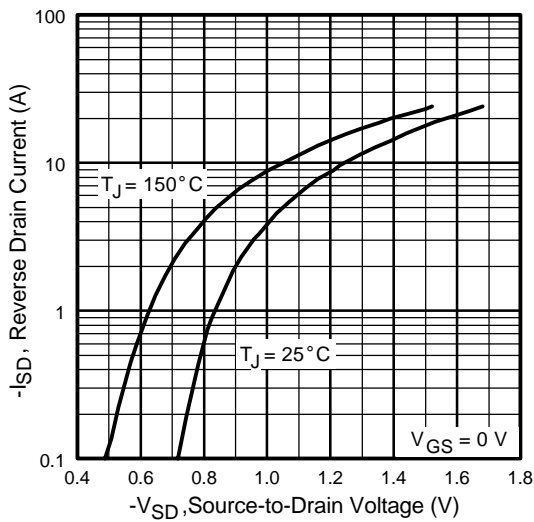


Fig 7. Typical Source-Drain Diode Forward Voltage

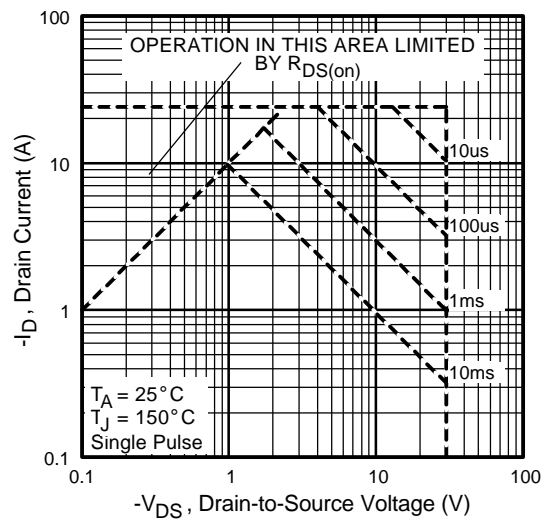


Fig 8. Maximum Safe Operating Area

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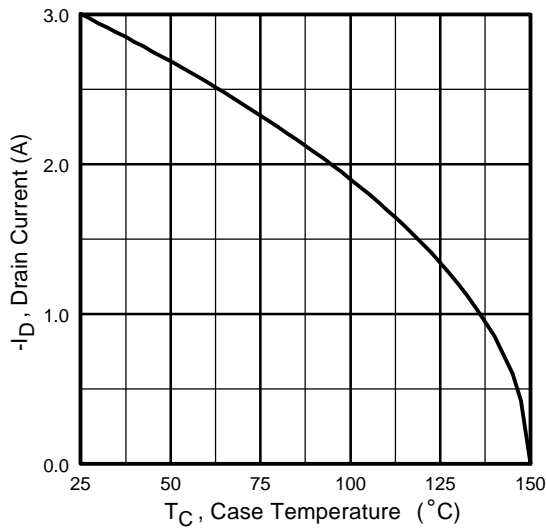


Fig 9. Maximum Drain Current Vs. Case Temperature

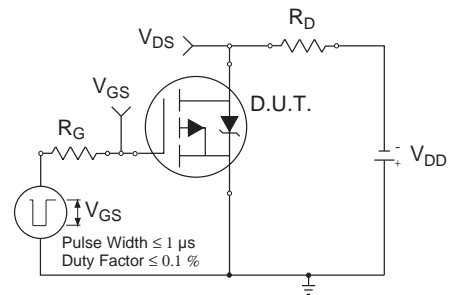


Fig 10a. Switching Time Test Circuit

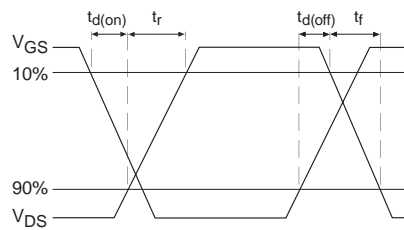


Fig 10b. Switching Time Waveforms

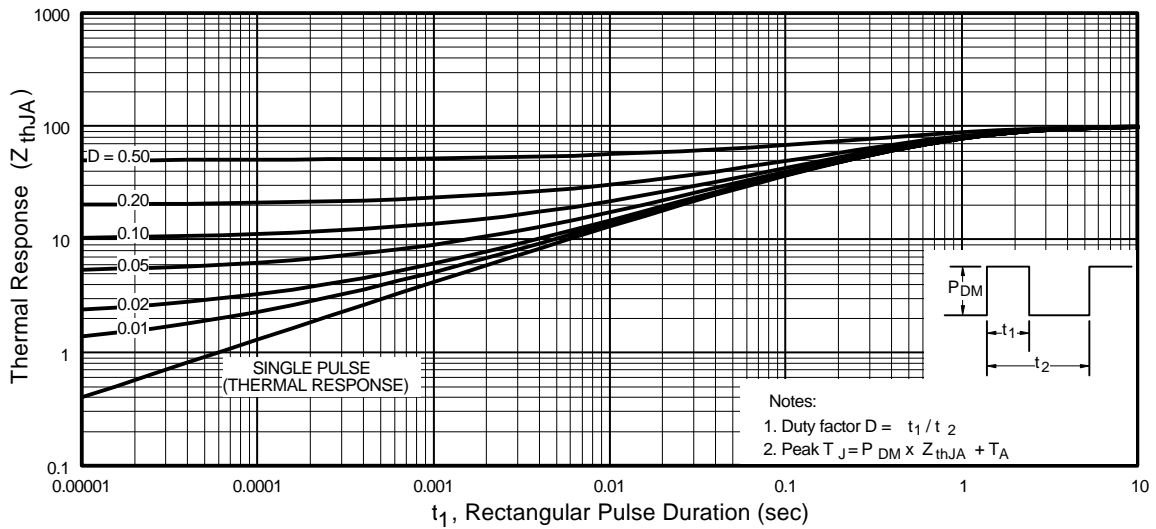


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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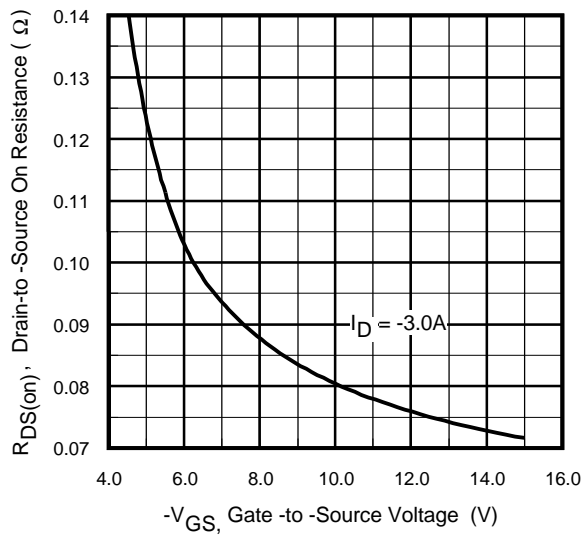


Fig 11. Typical On-Resistance Vs. Gate Voltage

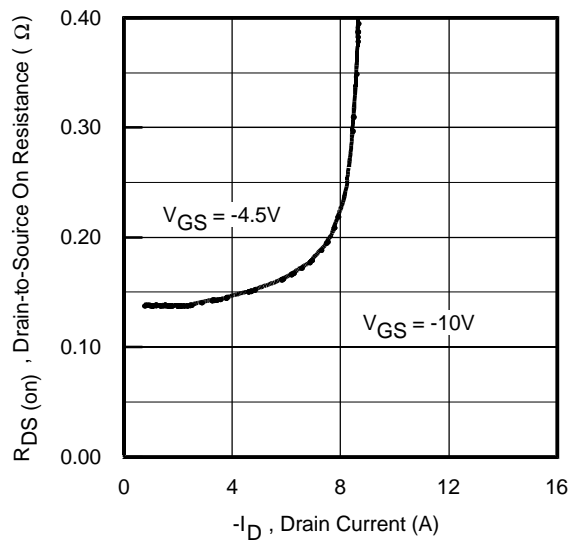


Fig 12. Typical On-Resistance Vs. Drain Current

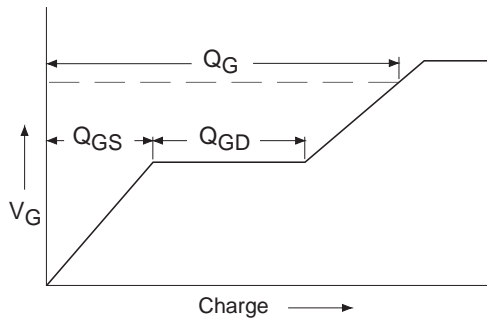


Fig 13a. Basic Gate Charge Waveform

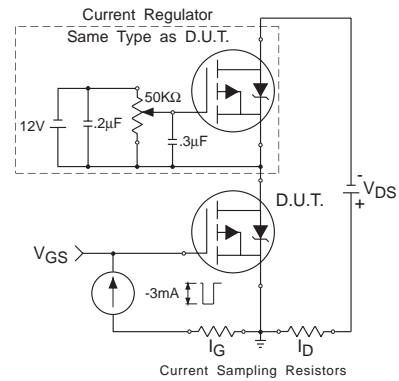


Fig 13b. Gate Charge Test Circuit

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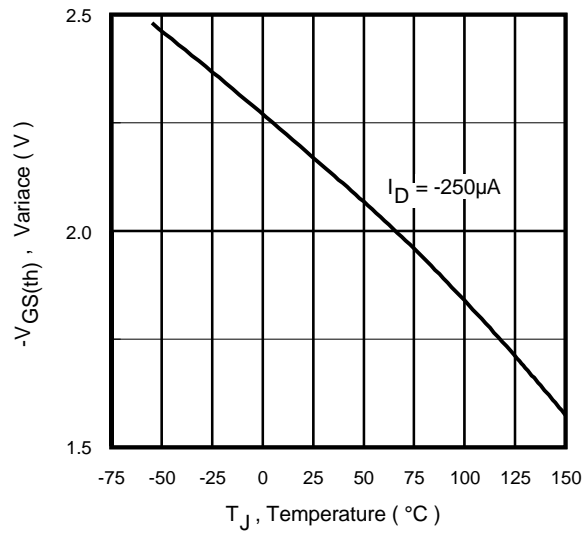


Fig 14. Threshold Voltage Vs. Temperature

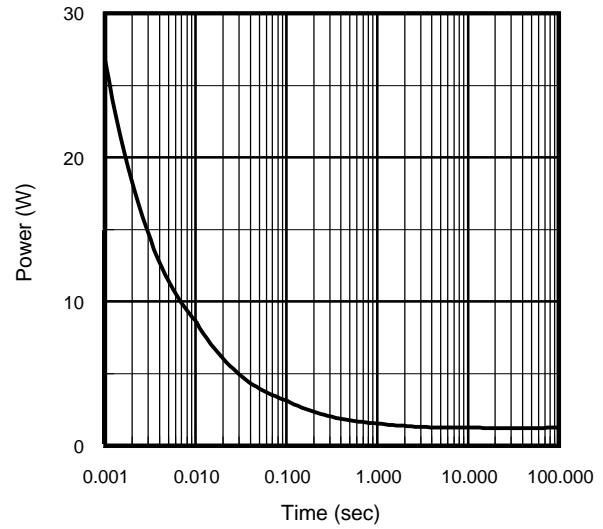


Fig 15. Typical Power Vs. Time

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)